BT134-800

4Q Triac

Rev.01 - 27 April 2018 Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT82 (SIP3) plastic package intended for use in general purpose bidirectional switching and phase control applications.

2. Features and benefits

- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Less sensitive gate for improved noise immunity
- Triggering in all four quadrants
- Compact package

3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control

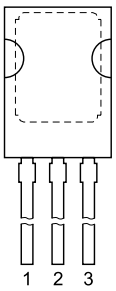
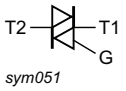
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values				Unit
Absolute maximum rating							
V_{DRM}	repetitive peak off-state voltage		800				V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 107$ °C; Fig. 1; Fig. 2; Fig. 3	4				A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig. 4; Fig. 5	25				A
Symbol	**Parameter**	**Conditions**		**Min**	**Typ**	**Max**	**Unit**
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12$ V; $I_T = 0.1$ A; T2+ G+; $T_j = 25$ °C; Fig. 7		-	5	35	mA
		$V_D = 12$ V; $I_T = 0.1$ A; T2+ G-; $T_j = 25$ °C; Fig. 7		-	8	35	mA
		$V_D = 12$ V; $I_T = 0.1$ A; T2- G-; $T_j = 25$ °C; Fig. 7		-	11	35	mA
		$V_D = 12$ V; $I_T = 0.1$ A; T2- G+; $T_j = 25$ °C; Fig. 7		-	30	70	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		 sym051
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT134-800	SIP3	plastic single-ended package; 3-leads (in-line)	SOT82

7. Marking

Table 4. Marking codes

Type number	Marking codes
BT134-800	BT134-800

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 107$ °C; Fig 1; Fig 2; Fig 3	4	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig 4; Fig 5	25	A
		full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms	27	A
I^2t	I^2t for fusing	$t_P = 10$ ms; SIN	3.1	A^2s
dI_T/dt	rate of rise of on-state current	$I_G = 70$ mA; T2+ G+	50	A/µs
		$I_G = 70$ mA; T2+ G-	50	A/µs
		$I_G = 70$ mA; T2- G-	50	A/µs
		$I_G = 140$ mA; T2- G+	10	A/µs
I_{GM}	peak gate current		2	A
P_{GM}	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T_{stg}	storage temperature		-40 to 150	°C
T_j	junction temperature		125	°C

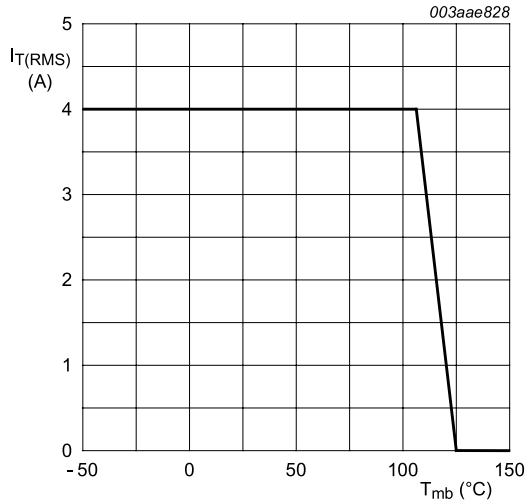
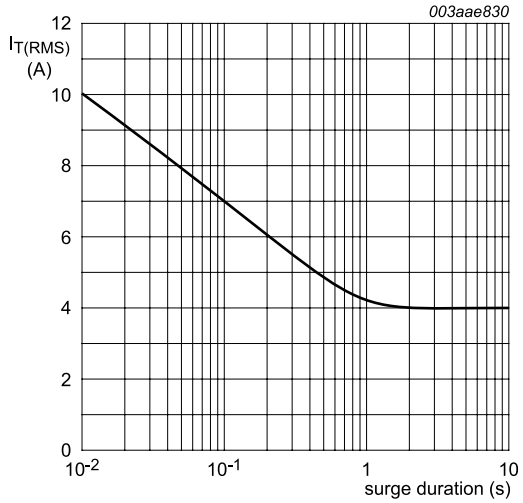
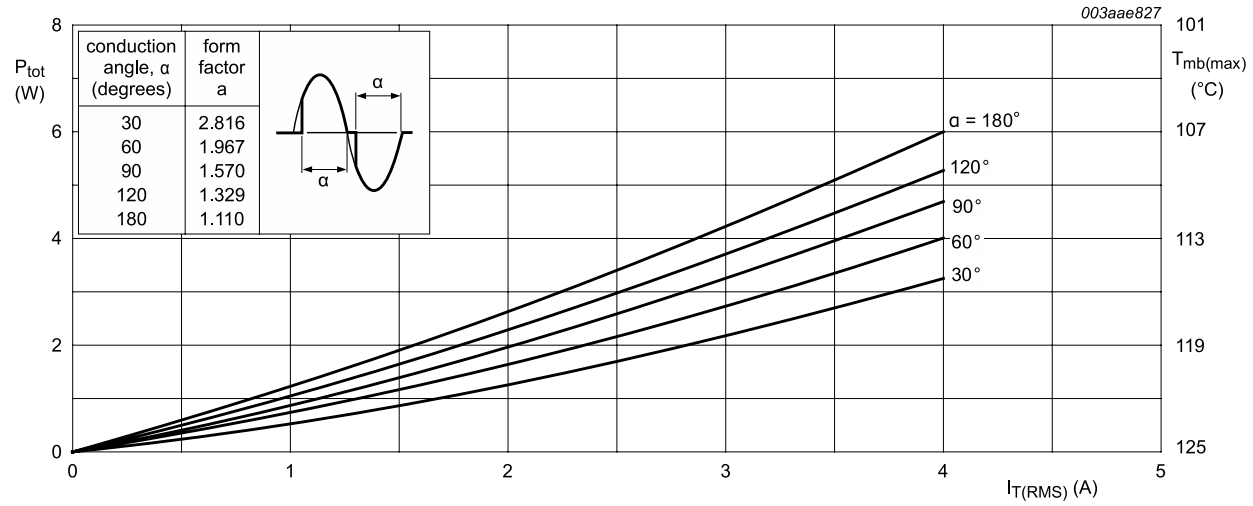


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz; $T_{mb} \leq 107$ °C

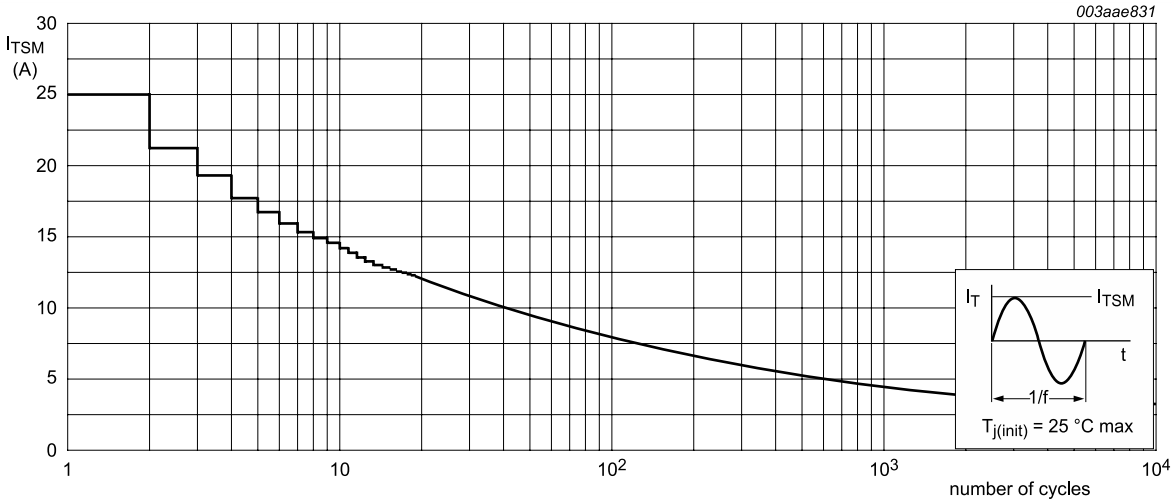
Fig. 2. RMS on-state current as a function of surge duration; maximum values



α = conduction angle

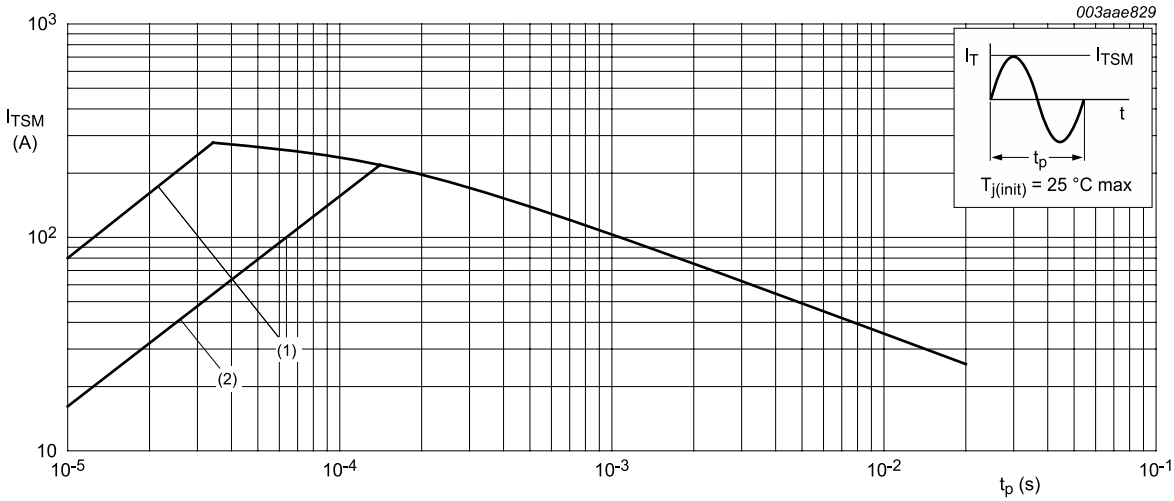
a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20$ ms

(1) dI_T/dt limit

(2) T2- G+ quadrant limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	half cycle; Fig 6		-	-	3.7	K/W
		full cycle; Fig 6		-	-	3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	100	-	K/W

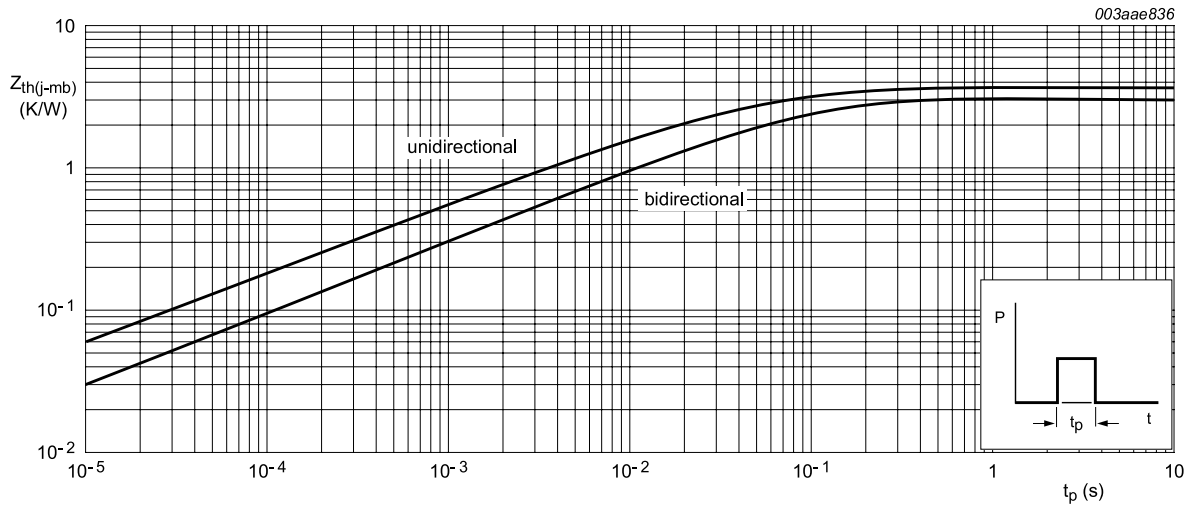
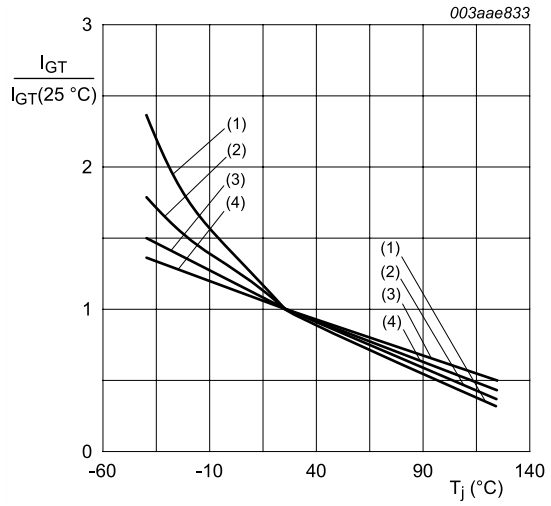


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 7		-	5	35	mA
		V_D = 12 V; I_T = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 7		-	8	35	mA
		V_D = 12 V; I_T = 0.1 A; T2- G-; T_j = 25 °C; Fig. 7		-	11	35	mA
		V_D = 12 V; I_T = 0.1 A; T2- G+; T_j = 25 °C; Fig. 7		-	30	70	mA
I_L	latching current	V_D = 12 V; I_G = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 8		-	7	20	mA
		V_D = 12 V; I_G = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 8		-	16	30	mA
		V_D = 12 V; I_G = 0.1 A; T2- G-; T_j = 25 °C; Fig. 8		-	5	20	mA
		V_D = 12 V; I_G = 0.1 A; T2- G+; T_j = 25 °C; Fig. 8		-	7	30	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	5	15	mA
V_T	on-state voltage	I_T = 5 A; T_j = 25 °C; Fig. 10		-	1.4	1.7	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 11		-	0.7	1	V
		V_D = 400 V; I_T = 0.1 A; T_j = 125 °C; Fig. 11		0.25	0.4	-	V
I_D	off-state current	V_D = 800 V; T_j = 125 °C		-	0.1	0.5	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		100	250	-	V/µs
dV_{com}/dt	rate of change of commutating voltage	V_D = 400 V; T_j = 95 °C; dI_{com}/dt = 1.8 A/ms; I_T = 4 A; gate open circuit		-	50	-	V/µs
t_{gt}	gate-controlled turn-on time	V_D = 800 V; I_{TM} = 6 A; I_G = 0.1 A; dI_G/dt = 5 A/µs		-	2	-	µs



(1) T2- G+
(2) T2- G-
(3) T2+ G-
(4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

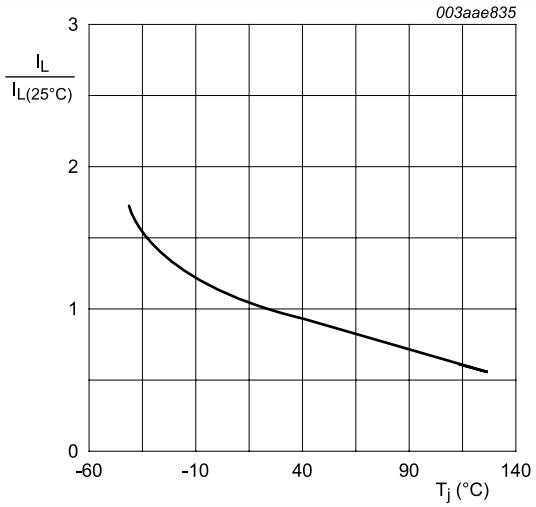


Fig. 8. Normalized latching current as a function of junction temperature

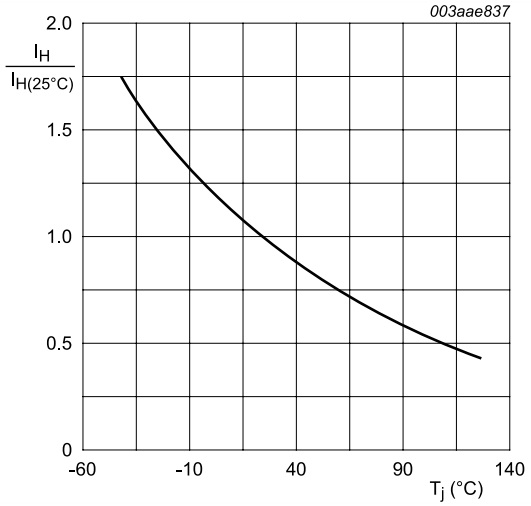
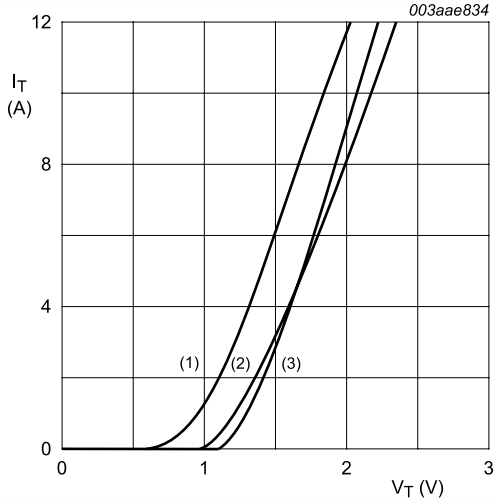


Fig. 9. Normalized holding current as a function of junction temperature



V_o = 1.27 V; R_s = 0.091 Ω
(1) T_j = 125 °C; typical values
(2) T_j = 125 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

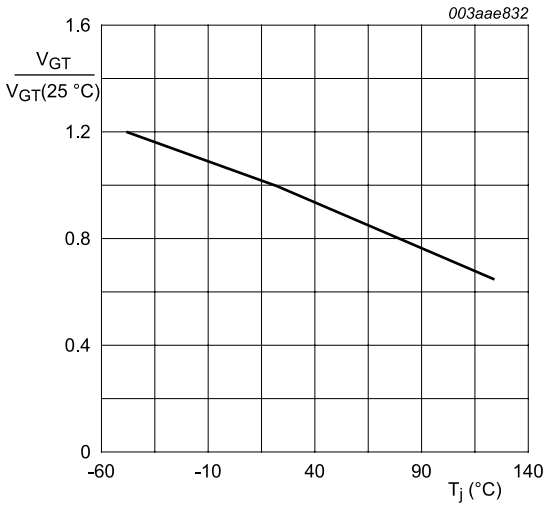
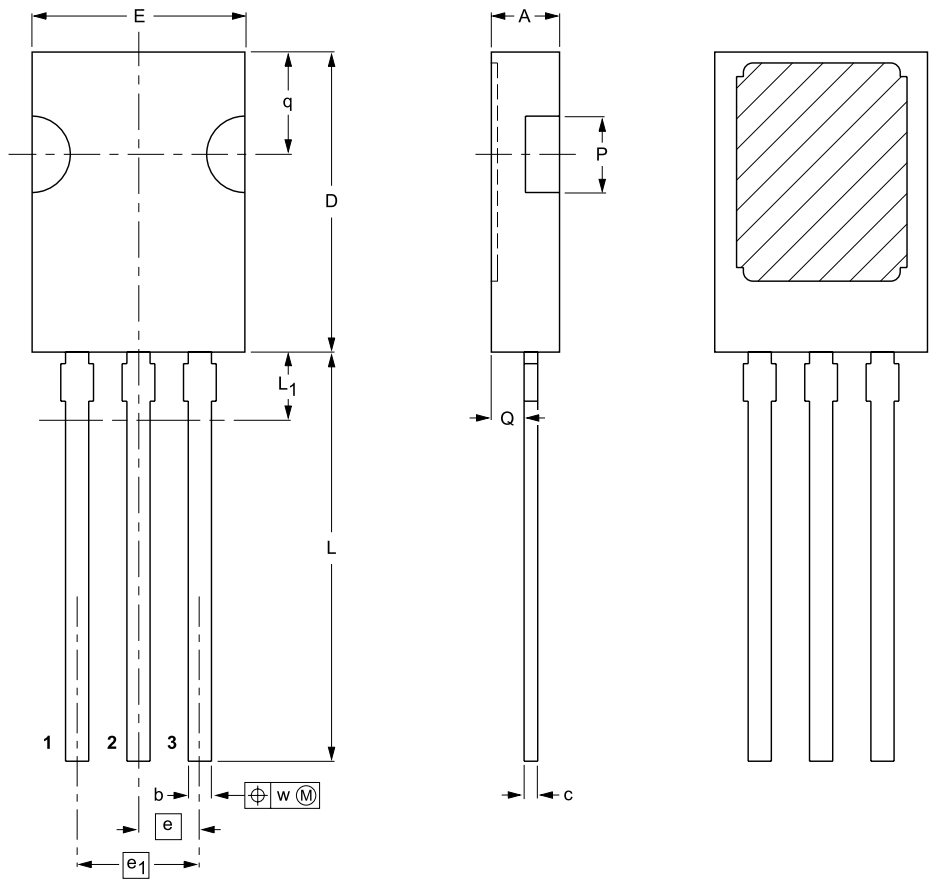


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

Plastic single-ended package; 3 leads (in-line) **SOT82**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	c	D	E	e	e_1	L	L_1 (1) max.	P	Q	q	w
mm	2.8 2.3	0.88 0.65	0.58 0.47	11.1 10.5	7.8 7.2	2.29	4.58	16.5 15.3	2.54	3.1 2.5	1.5 0.9	3.9 3.5	0.254

Note

1. Terminal dimensions within this zone are uncontrolled to allow for body and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT82						97-06-11

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".
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13. Contents

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Date of release: 27 April 2018

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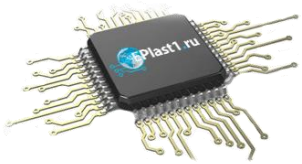

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